#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Peak Power Dissipation (Note 1) @ T <sub>L</sub> = 25°C, Pulse Width = 1 ms	P <sub>PK</sub>	600	W
DC Power Dissipation @ T <sub>L</sub> = 75°C Measured Zero Lead Length (Note 2) Derate Above 75°C Thermal Resistance from Junction–to–Lead	$P_{D}$ $R_{ hetaJL}$	3.0 40 25	W mW/°C °C/W
DC Power Dissipation (Note 3) @ T <sub>A</sub> = 25°C Derate Above 25°C Thermal Resistance from Junction–to–Ambient	$P_{D}$ $R_{ heta JA}$	0.55 4.4 226	W mW/°C °C/W
Forward Surge Current (Note 4) @ T <sub>A</sub> = 25°C	I <sub>FSM</sub>	100	Α
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	−65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

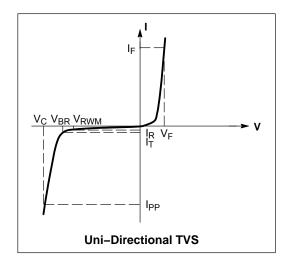
- 1. 10 X 1000 μs, non-repetitive
- 1" square copper pad, FR-4 board
   FR-4 board, using Littelfuse minimum recommended footprint, as shown in 403A case outline dimensions spec.
   1/2 sine wave (or equivalent square wave), PW = 8.3 ms, duty cycle = 4 pulses per minute maximum.

### **ELECTRICAL CHARACTERISTICS**

( $T_A$  = 25°C unless otherwise noted,  $V_F$  = 3.5 V Max. @  $I_F$ (Note 4) = 30 A, V<sub>F</sub> = 1.3 V Max. @ I<sub>F</sub> (Note 4) = 3 A) (Note 5)

Symbol	Parameter
I <sub>PP</sub>	Maximum Reverse Peak Pulse Current
V <sub>C</sub>	Clamping Voltage @ I <sub>PP</sub>
V <sub>RWM</sub>	Working Peak Reverse Voltage
I <sub>R</sub>	Maximum Reverse Leakage Current @ V <sub>RWM</sub>
V <sub>BR</sub>	Breakdown Voltage @ I <sub>T</sub>
I <sub>T</sub>	Test Current
ΘV <sub>BR</sub>	Maximum Temperature Coefficient of V <sub>BR</sub>
I <sub>F</sub>	Forward Current
V <sub>F</sub>	Forward Voltage @ I <sub>F</sub>

5. 1/2 sine wave or equivalent, PW = 8.3 ms, non-repetitive duty cycle



### **ELECTRICAL CHARACTERISTICS**

		V <sub>RWM</sub>	I <sub>R</sub> @	Breakdown Voltage				V <sub>C</sub> @ I <sub>PP</sub> (Note 8)			C <sub>typ</sub>	
	Device	(Note 6)	V <sub>RWM</sub>	V <sub>BR</sub> V (Not		V <sub>BR</sub> V (Note 7)		@ I <sub>T</sub>	V <sub>C</sub>	I <sub>PP</sub>	ΘV <sub>BR</sub>	(Note 9)
Device*	Marking	V	μΑ	Min	Nom	Max	mA	V	Α	%/°C	pF	
P6SMB6.8AT3G P6SMB7.5AT3G P6SMB8.2AT3G P6SMB9.1AT3G	6V8A 7V5A 8V2A 9V1A	5.8 6.4 7.02 7.78	1000 500 200 50	6.45 7.13 7.79 8.65	6.8 7.51 8.2 9.1	7.14 7.88 8.61 9.55	10 10 10 1	10.5 11.3 12.1 13.4	57 53 50 45	0.057 0.061 0.065 0.068	2380 2180 2015 1835	
P6SMB10AT3G P6SMB12AT3G P6SMB13AT3G	10A 12A 13A	8.55 10.2 11.1	10 5 5	9.5 11.4 12.4	10 12 13.05	10.5 12.6 13.7	1 1 1	14.5 16.7 18.2	41 36 33	0.073 0.078 0.081	1690 1435 1335	
P6SMB15AT3G P6SMB16AT3G P6SMB18AT3G P6SMB20AT3G	15A 16A 18A 20A	12.8 13.6 15.3 17.1	5 5 5 5	14.3 15.2 17.1 19	15.05 16 18 20	15.8 16.8 18.9 21	1 1 1 1	21.2 22.5 25.2 27.7	28 27 24 22	0.084 0.086 0.088 0.09	1175 1110 1000 910	
P6SMB22AT3G P6SMB24AT3G P6SMB27AT3G P6SMB30AT3G	22A 24A 27A 30A	18.8 20.5 23.1 25.6	5 5 5 5	20.9 22.8 25.7 28.5	22 24 27.05 30	23.1 25.2 28.4 31.5	1 1 1	30.6 33.2 37.5 41.4	20 18 16 14.4	0.092 0.094 0.096 0.097	835 775 700 635	
P6SMB33AT3G P6SMB36AT3G P6SMB39AT3G P6SMB43AT3G	33A 36A 39A 43A	28.2 30.8 33.3 36.8	5 5 5 5	31.4 34.2 37.1 40.9	33. <i>0</i> 5 36 39.05 43.05	34.7 37.8 41 45.2	1 1 1	45.7 49.9 53.9 59.3	13.2 12 11.2 10.1	0.098 0.099 0.1 0.101	585 540 500 460	
P6SMB47AT3G P6SMB51AT3G P6SMB56AT3G P6SMB62AT3G	47A 51A 56A 62A	40.2 43.6 47.8 53	5 5 5 5	44.7 48.5 53.2 58.9	47.05 51.05 56 62	49.4 53.6 58.8 65.1	1 1 1	64.8 70.1 77 85	9.3 8.6 7.8 7.1	0.101 0.102 0.103 0.104	425 395 365 335	
P6SMB68AT3G P6SMB75AT3G P6SMB91AT3G	68A 75A 91A	58.1 64.1 77.8	5 5 5	64.6 71.3 86.5	68 75.05 91	71.4 78.8 95.5	1 1 1	92 103 125	6.5 5.8 4.8	0.104 0.105 0.106	305 280 235	
P6SMB100AT3G P6SMB120AT3G P6SMB130AT3G	100A 120A 130A	85.5 102 111	5 5 5	95 114 124	100 120 130.5	105 126 137	1 1 1	137 165 179	4.4 3.6 3.3	0.106 0.107 0.107	215 185 170	
P6SMB150AT3G P6SMB160AT3G P6SMB180AT3G	150A 160A 180A	128 136 154	5 5 5	143 152 171	150.5 160 180	158 168 189	1 1 1	207 219 246	2.9 2.7 2.4	0.108 0.108 0.108	150 140 130	
P6SMB200AT3G	200A	171	5	190	200	210	1	274	2.2	0.108	115	

<sup>6.</sup> A transient suppressor is normally selected according to the working peak reverse voltage (V<sub>RWM</sub>), which should be equal to or greater than the DC or continuous peak operating voltage level.
7. V<sub>BR</sub> measured at pulse test current I<sub>T</sub> at an ambient temperature of 25°C.
8. Surge current waveform per Figure 2 and derate per Figure 3.
9. Bias Voltage = 0 V, F = 1 MHz, T<sub>J</sub> = 25°C
\* Include SZ-prefix devices where applicable.

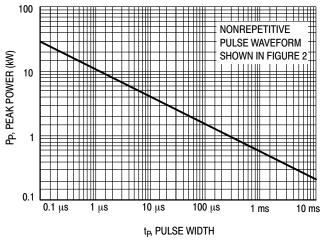


Figure 1. Pulse Rating Curve

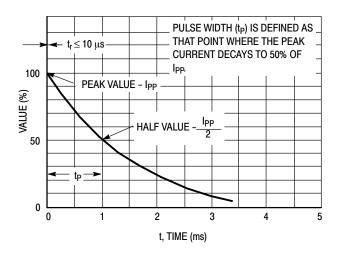


Figure 2. Pulse Waveform

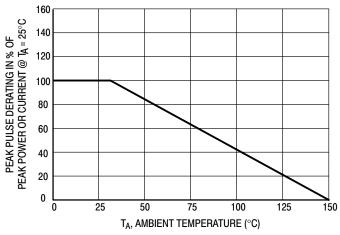


Figure 3. Pulse Derating Curve

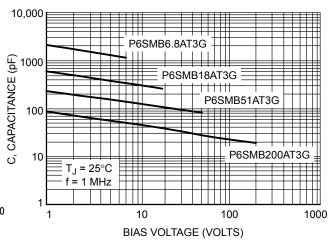
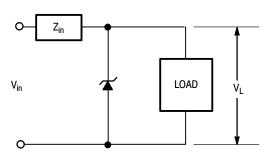


Figure 4. Typical Junction Capacitance vs. Bias Voltage

### **TYPICAL PROTECTION CIRCUIT**



#### **APPLICATION NOTES**

#### **Response Time**

In most applications, the transient suppressor device is placed in parallel with the equipment or component to be protected. In this situation, there is a time delay associated with the capacitance of the device and an overshoot condition associated with the inductance of the device and the inductance of the connection method. The capacitive effect is of minor importance in the parallel protection scheme because it only produces a time delay in the transition from the operating voltage to the clamp voltage as shown in Figure 5.

The inductive effects in the device are due to actual turn-on time (time required for the device to go from zero current to full current) and lead inductance. This inductive effect produces an overshoot in the voltage across the equipment or component being protected as shown in Figure 6. Minimizing this overshoot is very important in the application, since the main purpose for adding a transient suppressor is to clamp voltage spikes. The SMB series have a very good response time, typically < 1 ns and negligible inductance. However, external inductive effects could produce unacceptable overshoot. Proper circuit layout,

minimum lead lengths and placing the suppressor device as close as possible to the equipment or components to be protected will minimize this overshoot.

Some input impedance represented by  $Z_{in}$  is essential to prevent overstress of the protection device. This impedance should be as high as possible, without restricting the circuit operation.

### **Duty Cycle Derating**

The data of Figure 1 applies for non-repetitive conditions and at a lead temperature of 25°C. If the duty cycle increases, the peak power must be reduced as indicated by the curves of Figure 7. Average power must be derated as the lead or ambient temperature rises above 25°C. The average power derating curve normally given on data sheets may be normalized and used for this purpose.

At first glance the derating curves of Figure 7 appear to be in error as the 10 ms pulse has a higher derating factor than the 10  $\mu$ s pulse. However, when the derating factor for a given pulse of Figure 7 is multiplied by the peak power value of Figure 1 for the same pulse, the results follow the expected trend.

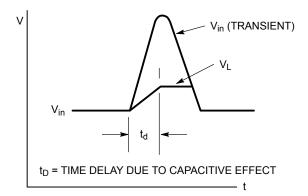


Figure 5.

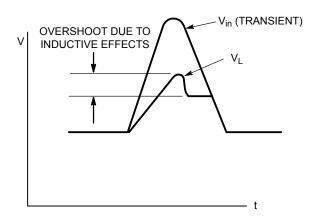


Figure 6.

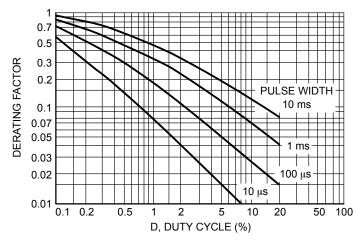


Figure 7. Typical Derating Factor for Duty Cycle

#### **UL RECOGNITION**

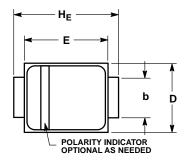
The entire series has *Underwriters Laboratory Recognition* for the classification of protectors (QVGQ2) under the UL standard for safety 497B and File #E128662. Many competitors only have one or two devices recognized or have recognition in a non-protective category. Some competitors have no recognition at all. With the UL497B recognition, our parts successfully passed several tests

including Strike Voltage Breakdown test, Endurance Conditioning, Temperature test, Dielectric Voltage-Withstand test, Discharge test and several more.

Whereas, some competitors have only passed a flammability test for the package material, we have been recognized for much more to be included in their Protector category.

#### PACKAGE DIMENSIONS

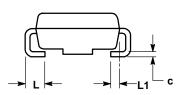
#### **SMB** CASE 403A-03 **ISSUE J**

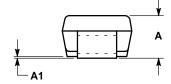




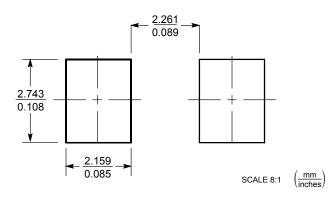
- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
- 2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION b SHALL BE MEASURED WITHIN DIMENSION L1.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	MOM	MAX	
Α	1.95	2.30	2.47	0.077	0.091	0.097	
A1	0.05	0.10	0.20	0.002	0.004	0.008	
b	1.96	2.03	2.20	0.077	0.080	0.087	
С	0.15	0.23	0.31	0.006	0.009	0.012	
D	3.30	3.56	3.95	0.130	0.140	0.156	
E	4.06	4.32	4.60	0.160	0.170	0.181	
HE	5.21	5.44	5.60	0.205	0.214	0.220	
L	0.76	1.02	1.60	0.030	0.040	0.063	
L1	0.51 REF			0.020 RFF			





# **SOLDERING FOOTPRINT**



Littelfuse products are not designed for, and shall not be used for, any purpose (including, without limitation, automotive, military, aerospace, medical, life-saving, life-sustaining or nuclear facility applications, devices intended for surgical implant into the body, or any other application in which the failure or lack of desired operation of the product may result in personal injury, death, or property damage) other than those expressly set forth in applicable Littelfuse product documentation. Warranties granted by Littelfuse shall be deemed void for products used for any purpose not expressly set forth in applicable Littelfuse documentation. Littelfuse shall not be liable for any claims or damages arising out of products used in applications not expressly intended by Littelfuse as set forth in applicable Littelfuse documentation. The sale and use of Littelfuse products is subject to Littelfuse Terms and Conditions of Sale, unless otherwise agreed by Littelfuse.